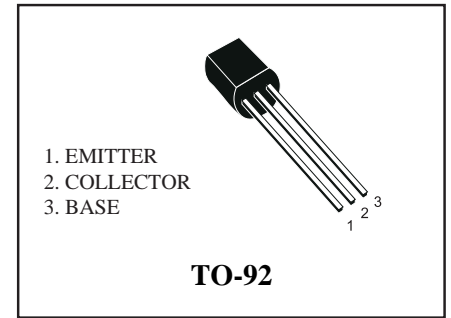


PNP Plastic-Encapsulate Transistor

(Pb) Lead(Pb)-Free

FEATURES :

- Low Saturation Medium Current Application



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	V _{CB0}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-8	V
Collector Current -Continuous	I _C	-0.7	A
Collector Power Dissipation	P _C	0.8	W
Thermal Resistance From Junction To Ambient	R _{θJA}	156	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

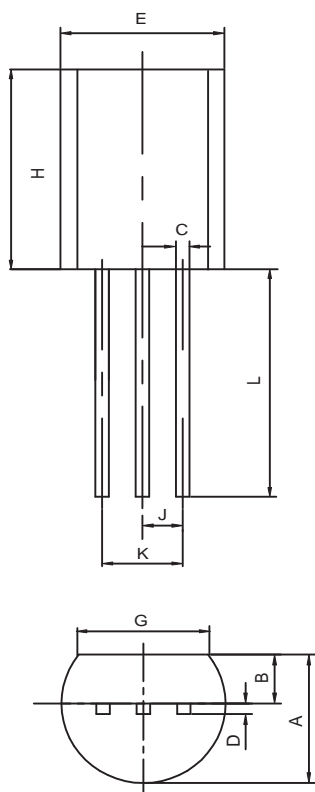
Parameter	Symbol	Test conditions	MIN	TYP	MAX	Units
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B =0	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -0.1mA, I _C =0	-8			V
Collector cut-off current	I _{CB0}	V _{CB} = -60V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -50mA	40		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-0.5A, I _B = -50mA			-0.7	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-0.5A, I _B =-50mA			-1.1	V
Transition Frequency	f _T	V _{CE} =-10V, I _C =-50mA		50		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		13		pF

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	120-240

TO-92 Outline Dimensions

unit:mm



TO-92		
Dim	Min	Max
A	3.30	3.70
B	1.10	1.40
C	0.38	0.55
D	0.36	0.51
E	4.40	4.70
G	3.43	-
H	4.30	4.70
J	1.270TYP	
K	2.44	2.64
L	14.10	14.50